ABSTRACT

METHOD AND APPARATUS FOR MANUFACTURING SEMICONDUCTOR DEVICES

There are disclosed a method and apparatus for manufacturing semiconductor devices. The surface of each semiconductor substrate (1, 11) is exposed to cyanide ions (CN^-) in order to reduce the density of interface states at the insulating film/semiconductor interface. For this purpose, the semiconductor substrate (1, 11) is immersed into a cyan compound solution or is exposed to a cyan compound gas, so that cyanide ions (CN^-) are bonded to dangling bonds at the surface of the semiconductor substrate (1, 11). As a result, the interface states at the insulating film/semiconductor interface can be reduced.

FIGURE 1